

Fig.1

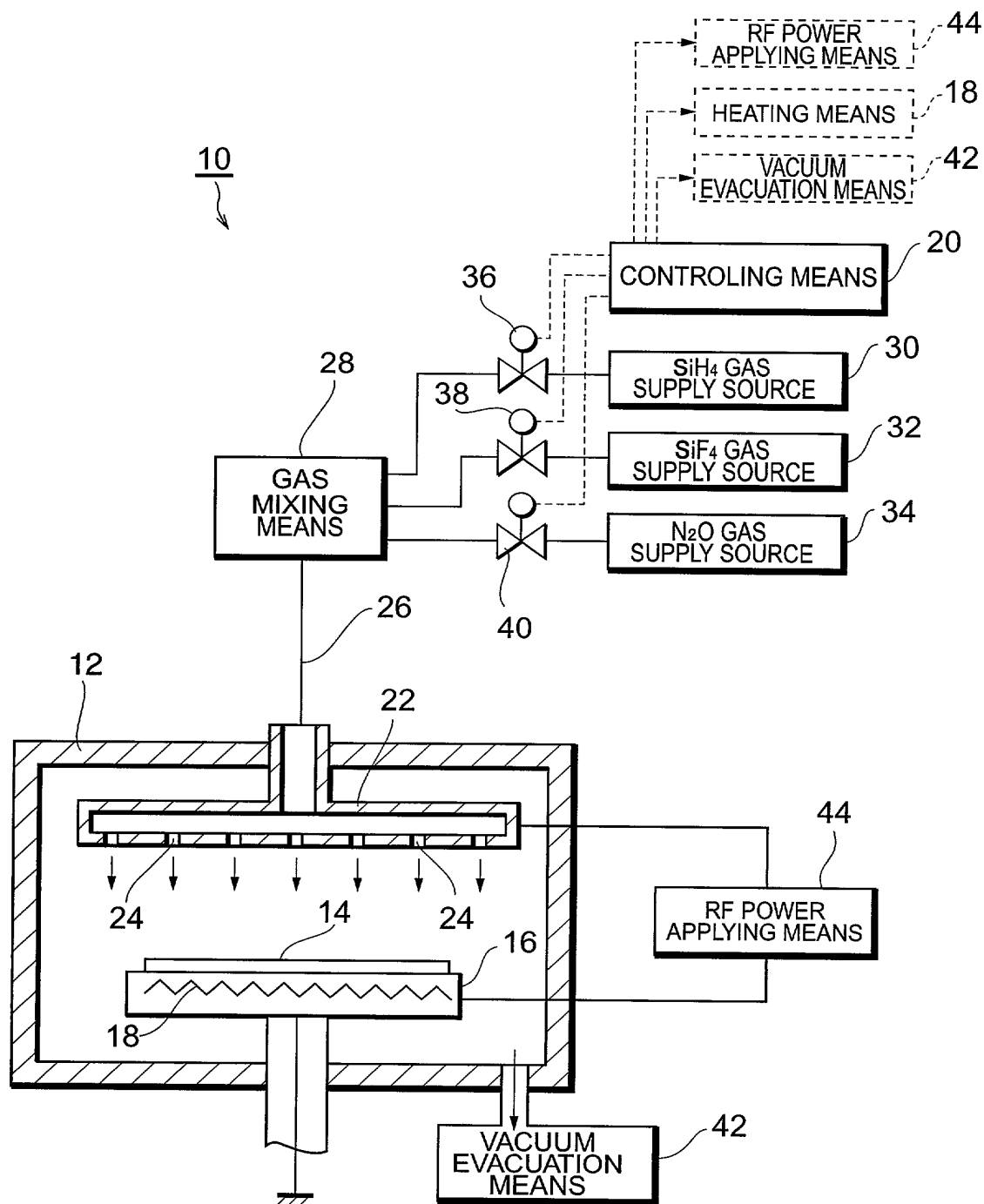


Fig.2A

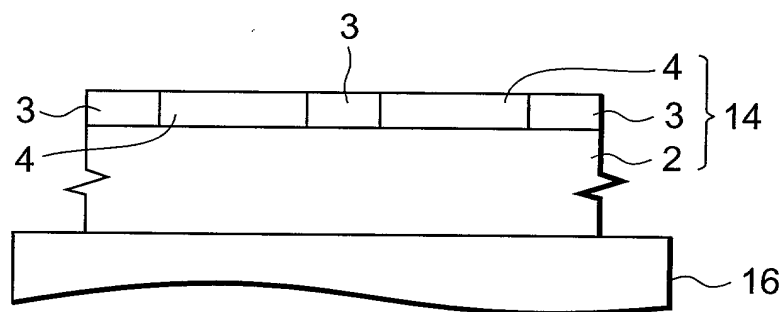


Fig.2B

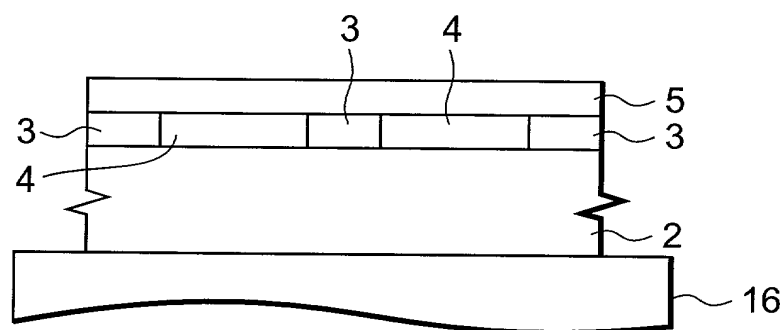


Fig.2C

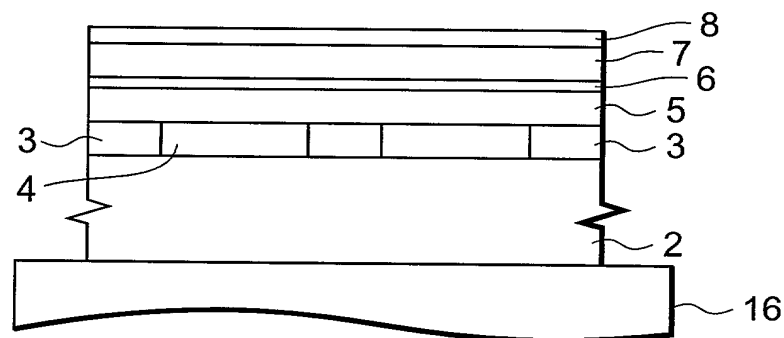


Fig.2D

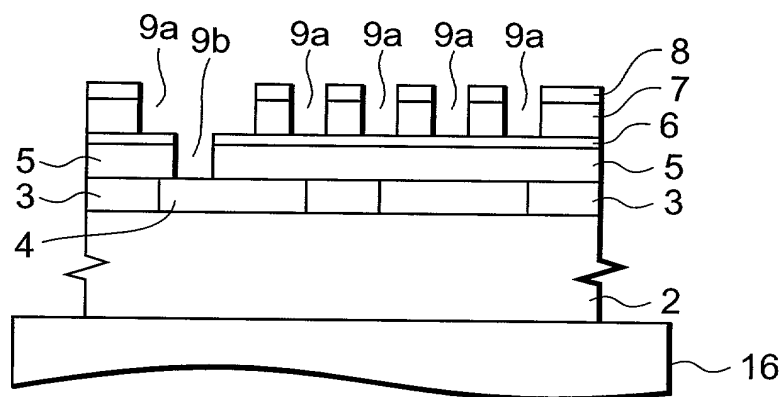


Fig.3

PARAMETER	TEST CONDITIONS	RAUGE OF VARIATION
13.56MHz RF POWER (W)	1500	1200~2000
PARALLEL PLATE ELECTRODE SEPARATION (cm)	1.0	1.0~1.75
CHAMBER PRESSURE (Pa)	493 (3.7Torr)	493~666 (3.7~5.0Torr)
TOTAL FLOW VOLUME(%)	100	100~200
N ₂ O FLOW VOLUME (sccm)	1500	1500~3000
SiH ₄ FLOW VOLUME (sccm)	115	115
SiF ₄ FLOW VOLUME (sccm)	130	50~250

Fig.4

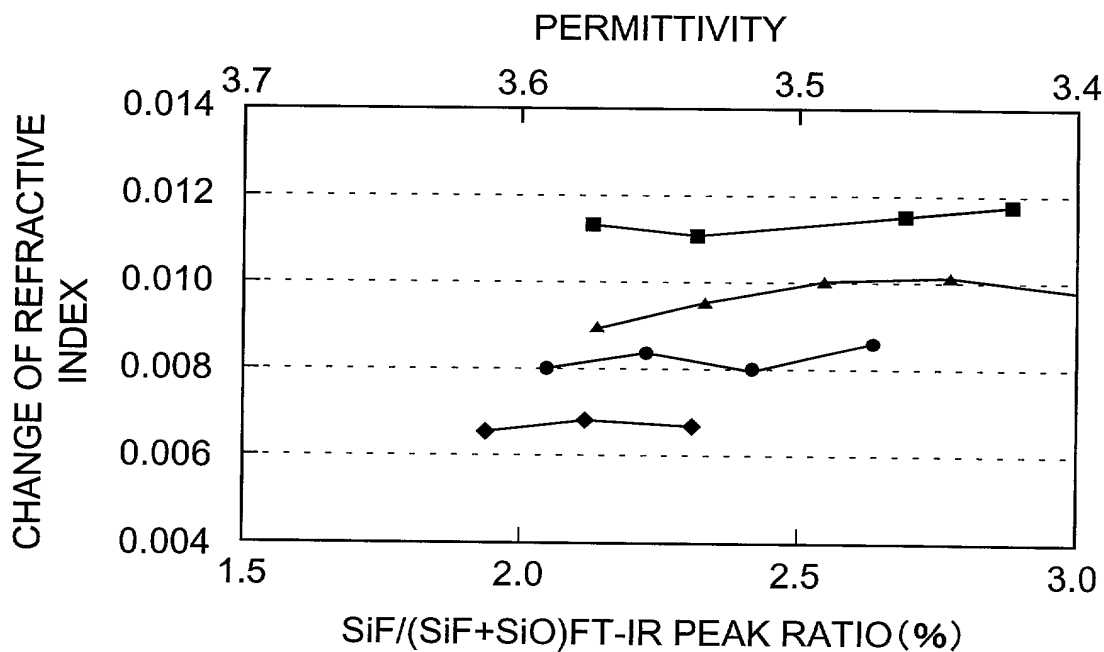


Fig.5

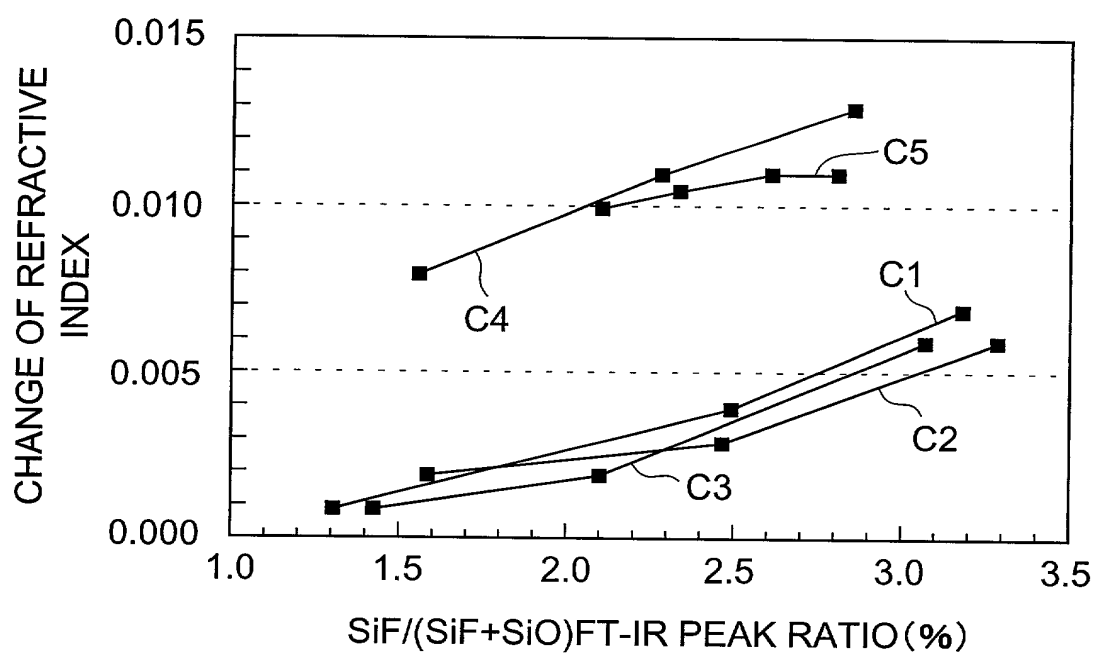


Fig.6

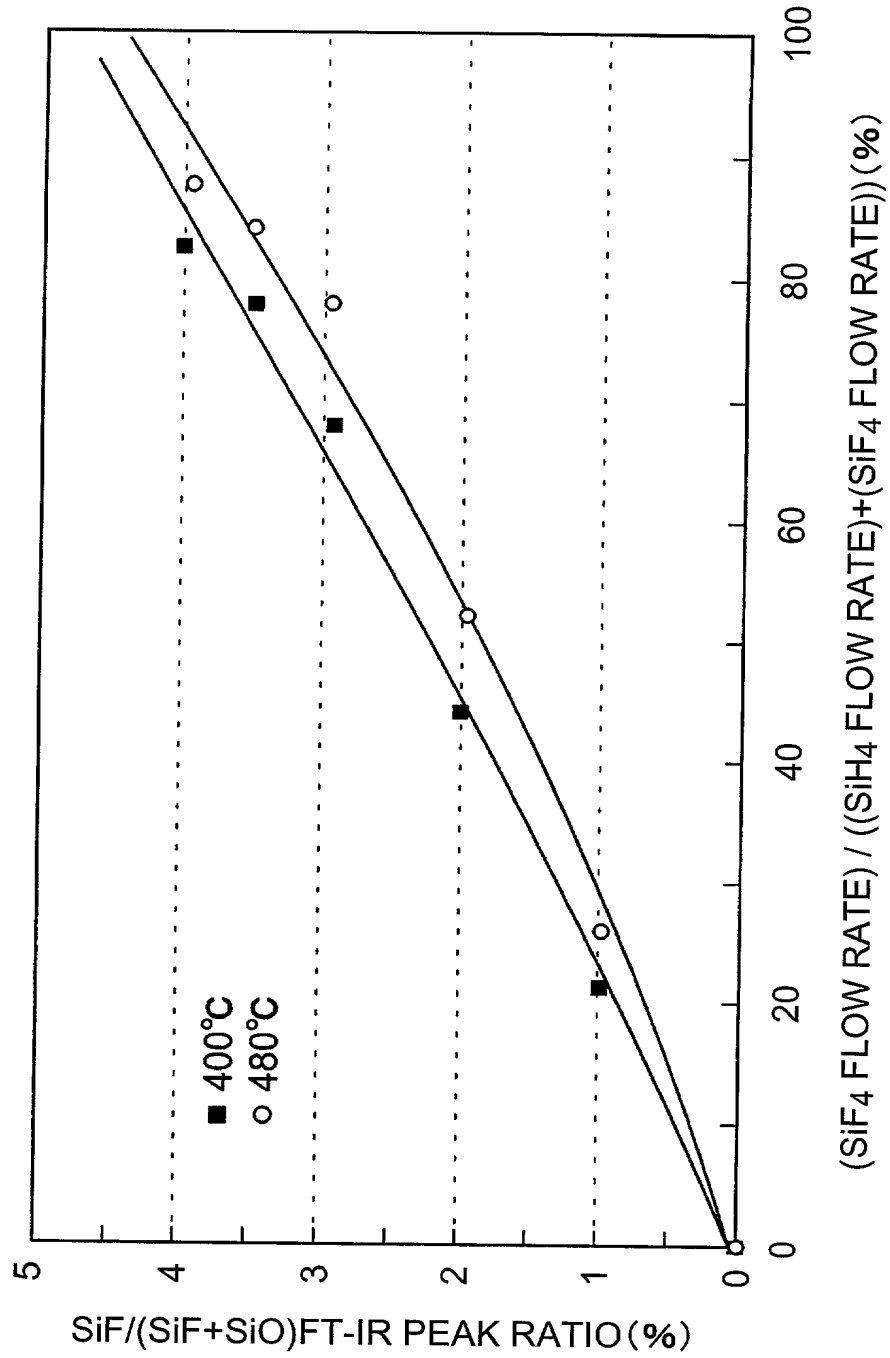


Fig.7

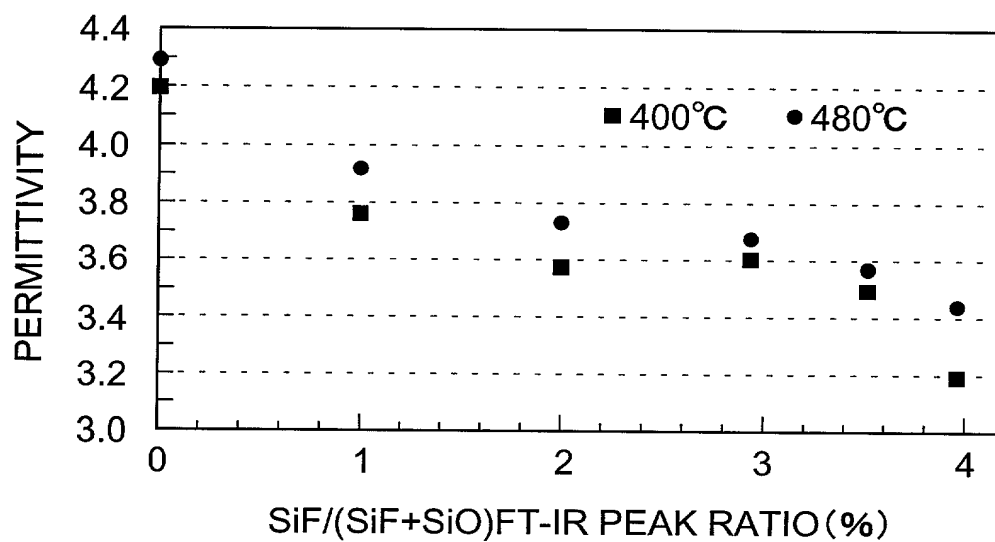


Fig.8

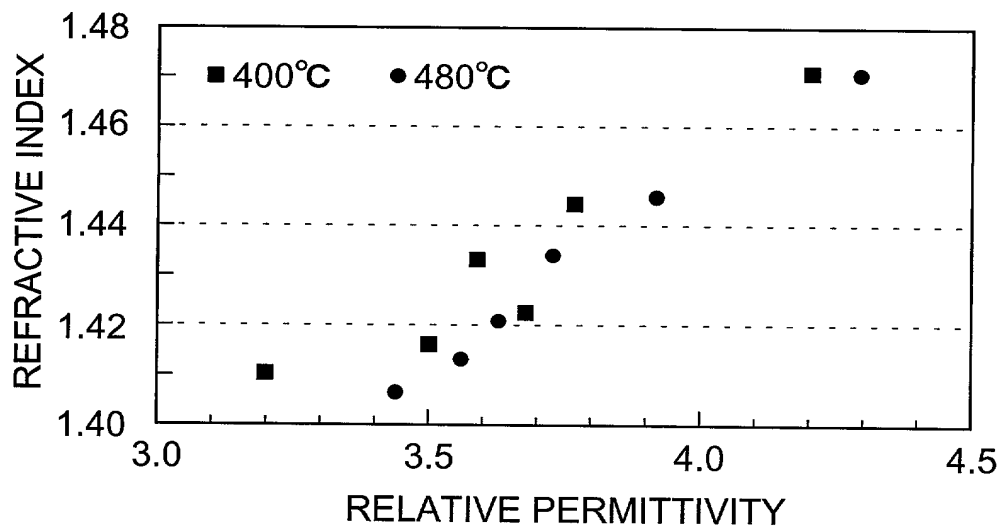


Fig.9

TYPE OF FILM		SiH ₄ FSG			TEOS FSG
FILM FORMING TEMPERAFURE		400°C	440°C	480°C	480°C
(SiOH+HOH)/SiO PEAK RATIO IN FT-IR AFTER LEFT IN CLEAN ROOM	LEFT FOR ONE WEEK	0.5	0.4	1.0	2.5
	LEFT FOR TWO WEEKS	0.7	1.1	0.7	—

Fig.10

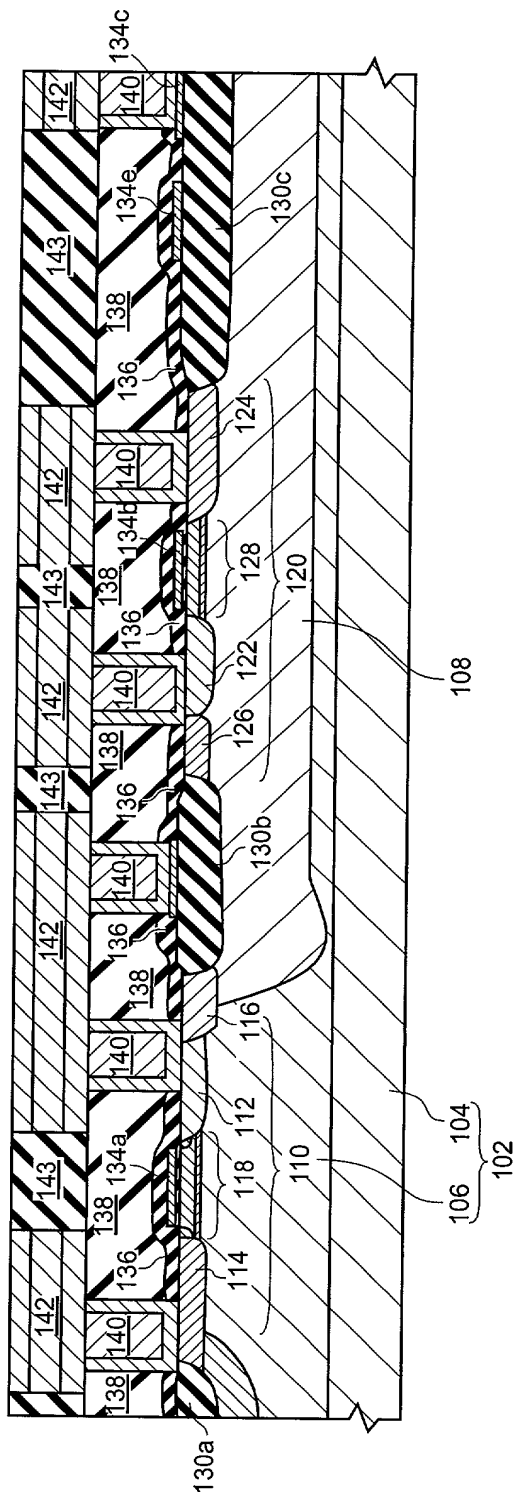


Fig.11

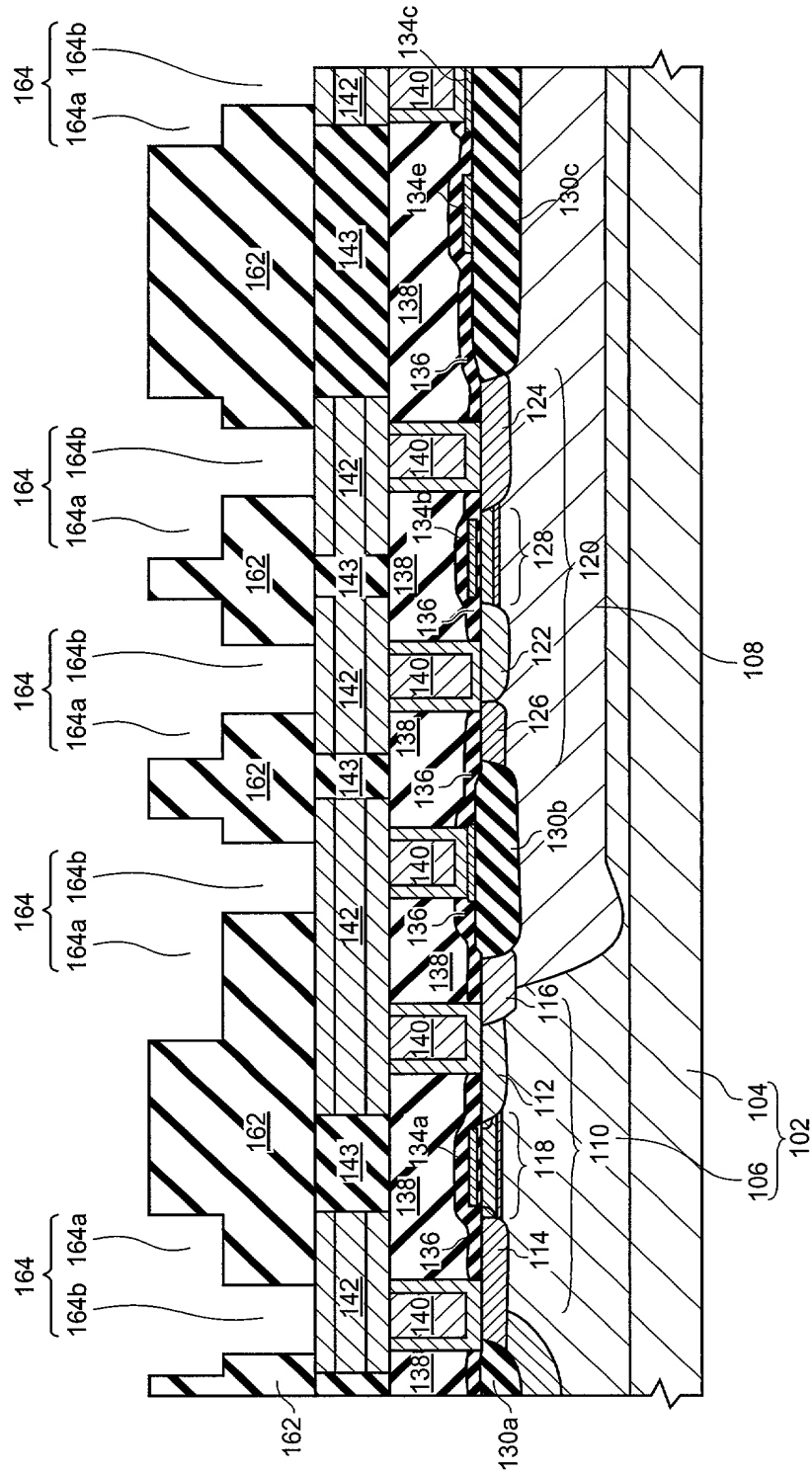


Fig.12

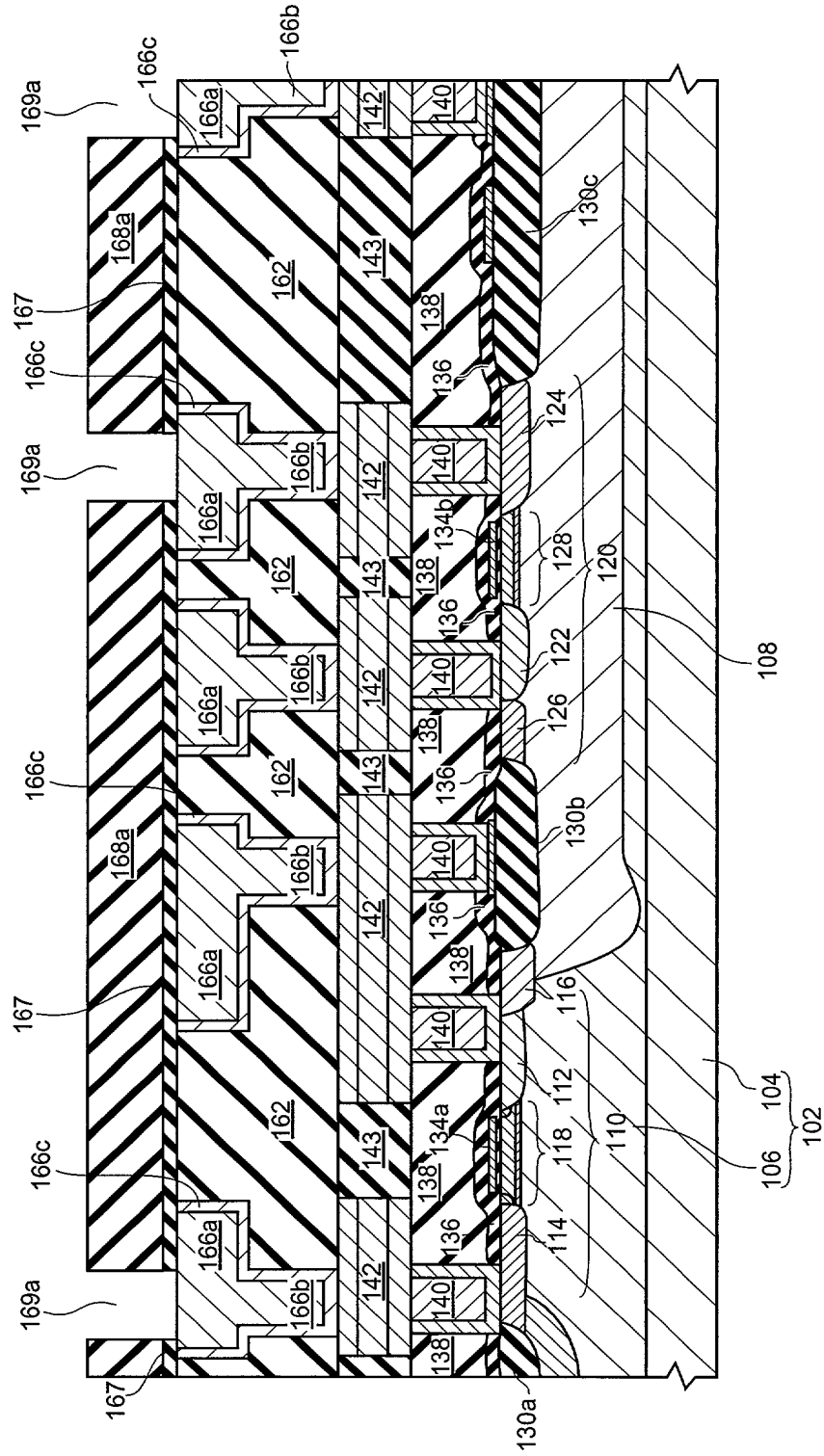


Fig. 13

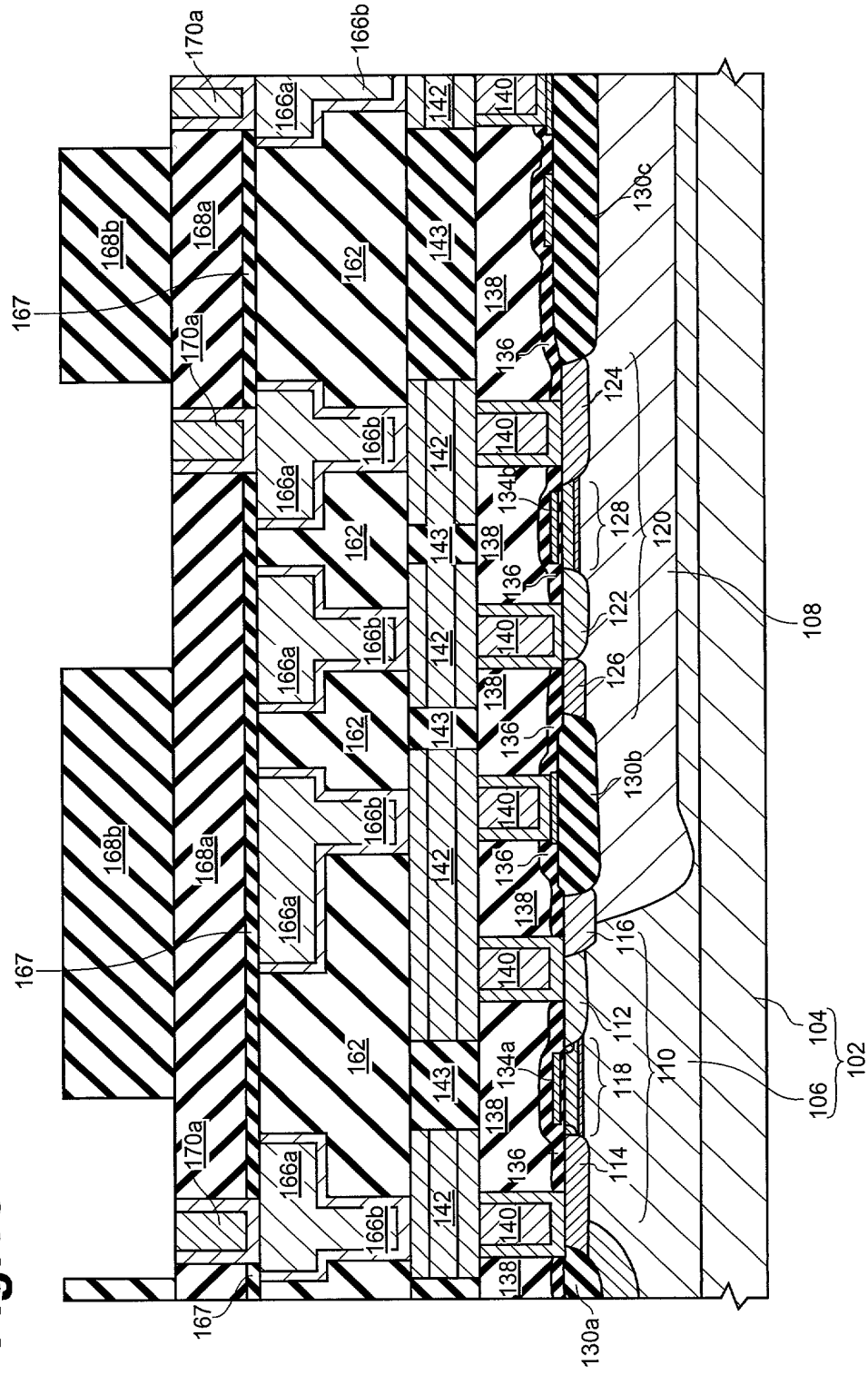


Fig. 14

